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N-Channel Enhancement Mode Field Effect Transistor in a PDFN 3 ˜3A-8L Plastic Package.

¤ª / Feats

V_{DS} (V) = 40V I_D =57A (V_{GS} = ±20V)

$R_{DS(ON)}$@10V ”5mR(Typ.4.5mR)

$R_{DS(ON)}$@4.5V ”10mR(Typ.6.2mR)

—)í D } ÄHF Product.

[redacted]

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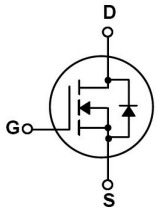
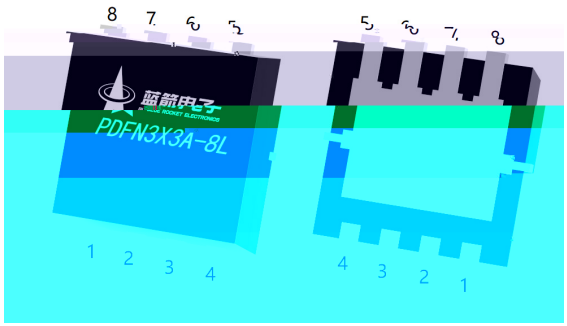
Load Switch Applications,Battery Power Management.





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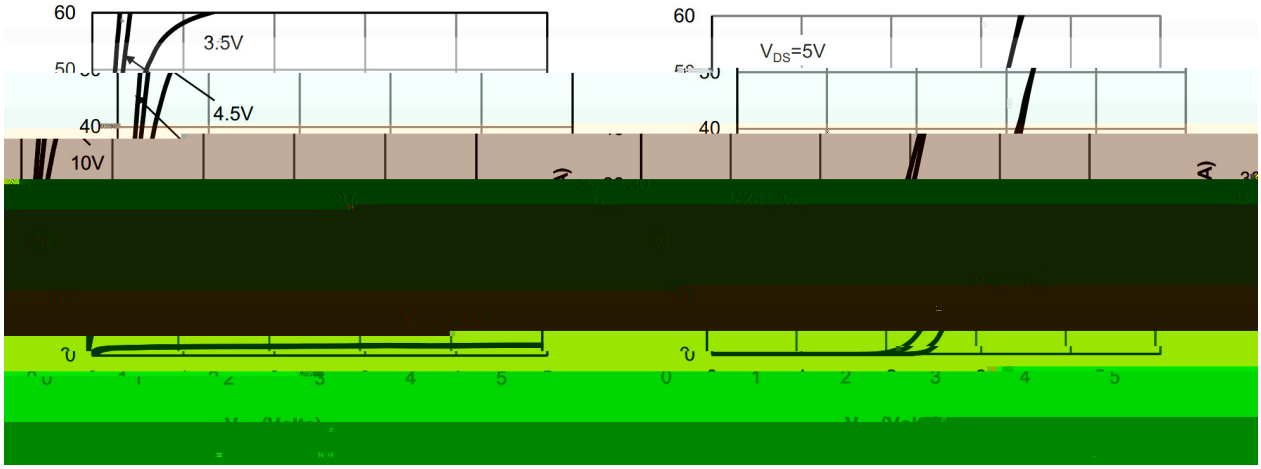
See Marking Instructions.

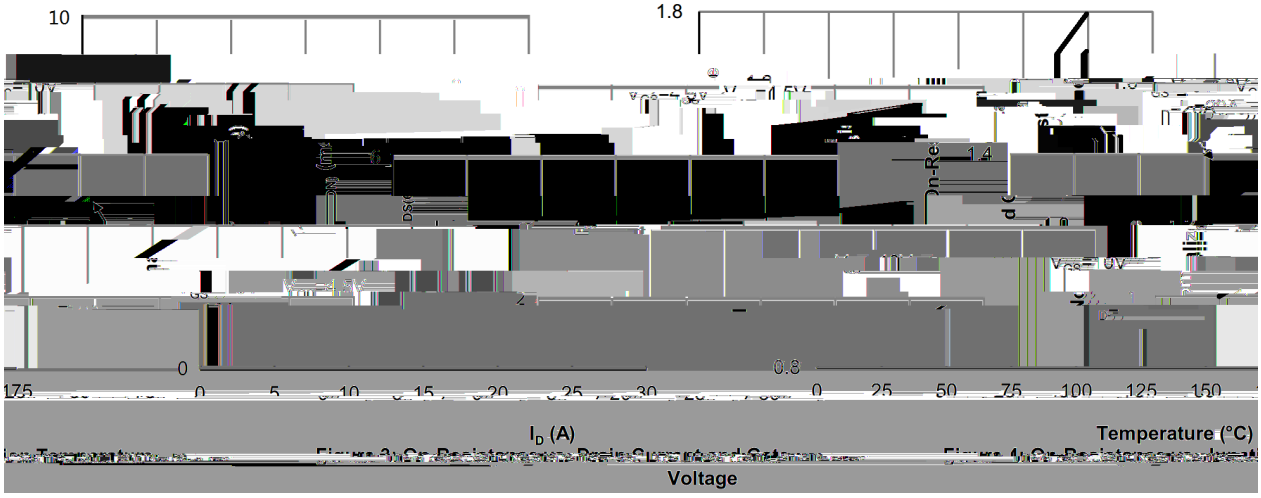
@ *f* Parameter	… Z Symbol	*f* › Rating	% y Unit
Drain-Source Voltage	V_{DSS}	40	V
Drain Current	I_D		

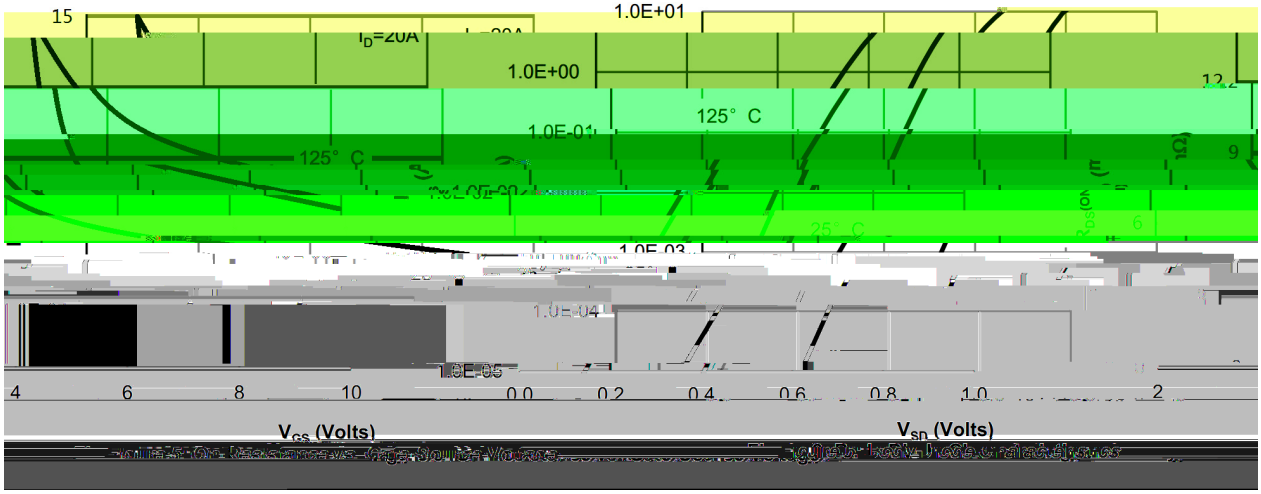
Ô4ì × ? d / Electrical Characteristics (Ta=25 ;)

@ ƒ Parameter	… Z Symbol	y ¡ Ú ^ Test Conditions	Â 4 › Min	Á º › Typ	Â Ý › Max	% y Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250 A	40	43		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=40V V_{GS}=0V			1	A
Gate-Body Leakage Current Forward	I_{GSS}	V_{GS}=±20V V_{DS}=0V			±0.1	A
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=250 A	1.0	1.7	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V I_D=20A		4.5	5	m
		V_{GS}=4.5V I_D=10A		6.2	10	m
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS}=0V I_S=1A			1.2	V
Input Capacitance	C_{iss}	V_{DS}=25V V_{GS}=0V f=1.0MHz		2900		pF
Output Capacitance	C_{oss}			210		
Reverse Transfer Capacitance	C_{rss}			200		
Gate resistance	R_g	V_{GS}=0V V_{DS}=0V f=1MHz		2.5		
Total Gate Charge	$Q_{g(10V)}$	V_{GS}=10V V_{DS}=20V I_D=20A		70		nC
Total Gate Charge	$Q_{g(4.5V)}$			15		
Gate Source Charge	Q_{gs}			15		
Gate Drain Charge	Q_{gd}			22		
Turn-On Delay Time	$t_{d(on)}$	V_{GS}=10V V_{DS}=20V R_L=1 R_{GEN}=3.0		15		ns
Turn-On Rise Time	t_r			30		
Turn-Off Delay Time	$t_{d(off)}$			54		
Turn-Off Fall Time	t_f			20		

Ô ? d • Ž ¢ / Electrical Characteristics







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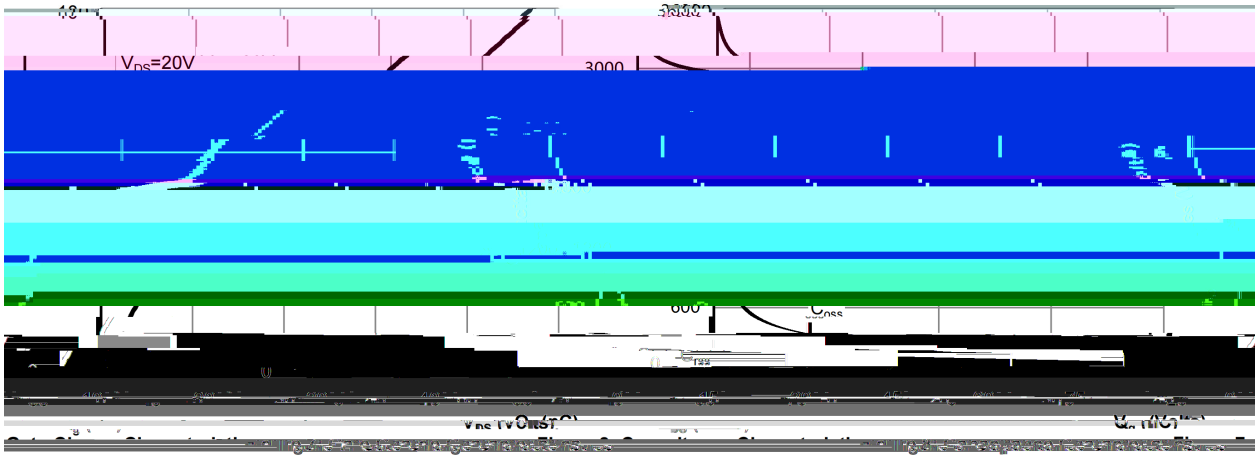

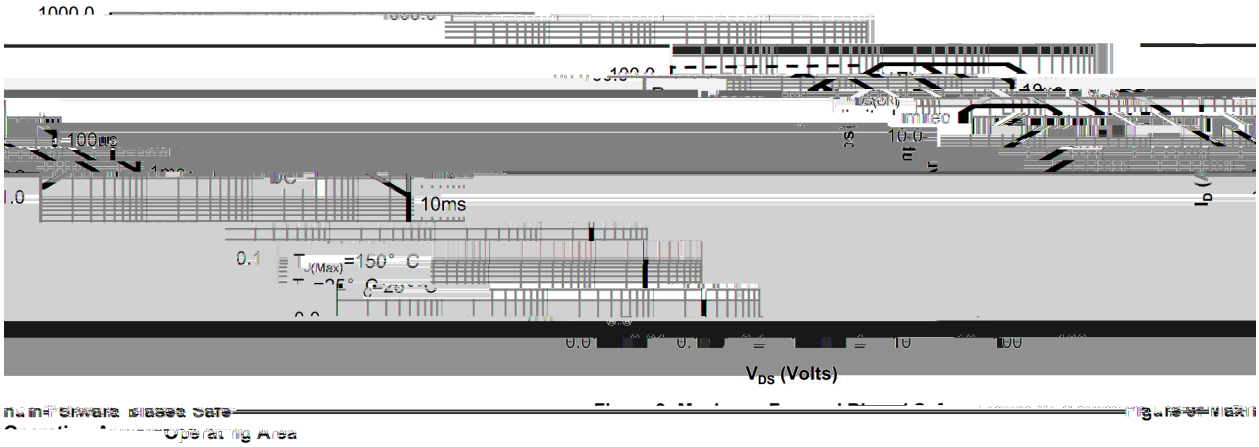

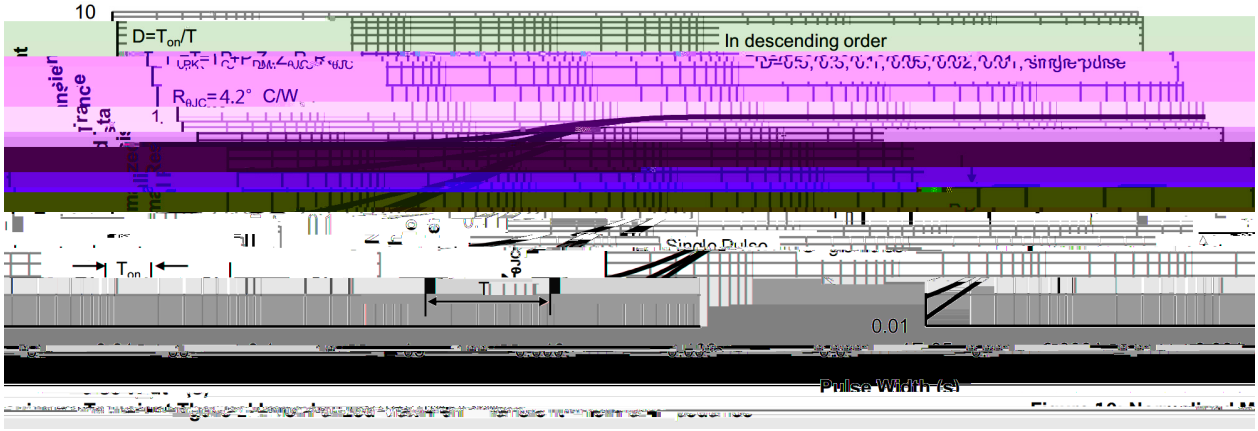

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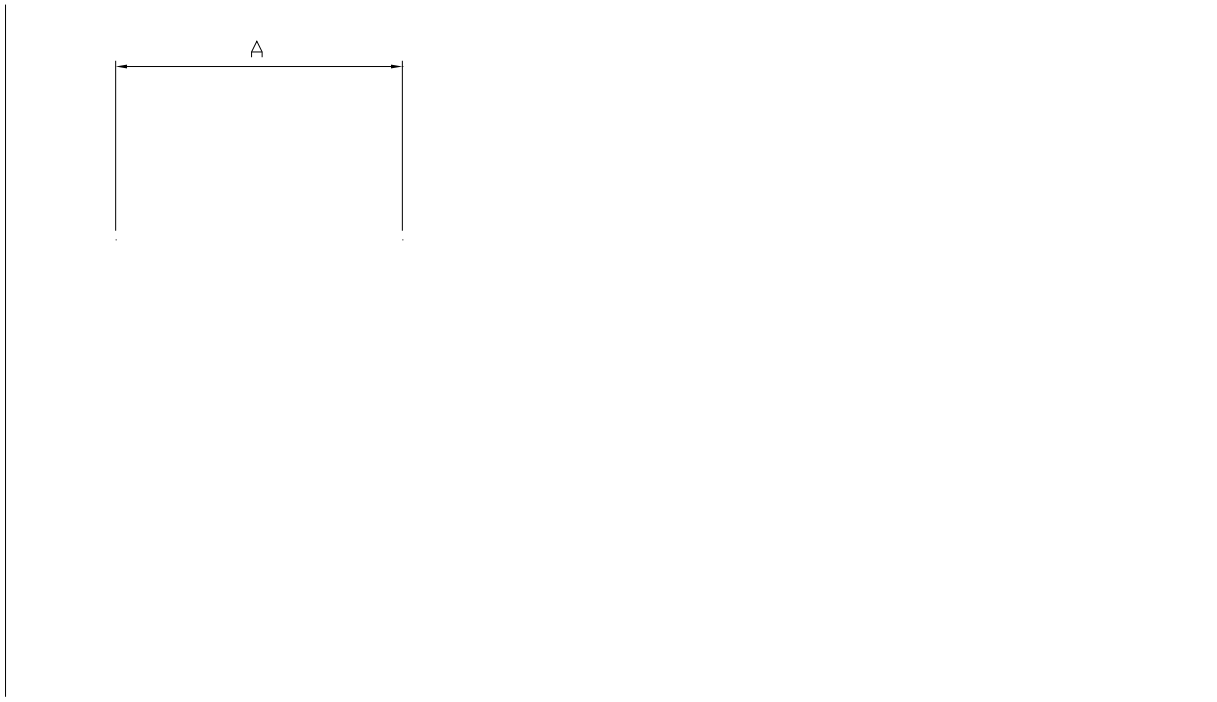
Unit:mm



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